



# STP22NE10L

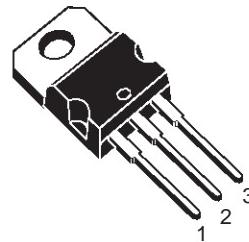
## N - CHANNEL 100V - 0.07 Ω - 22A TO-220 STripFET™ POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>D(on)</sub>	I <sub>D</sub>
STP22NE10L	100 V	< 0.085 Ω	22 A

- TYPICAL R<sub>D(on)</sub> = 0.07 Ω
- LOW THRESHOLD DRIVE
- LOGIC LEVEL DEVICE

### DESCRIPTION

This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

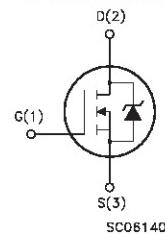


TO-220

### APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- SOLENOID AND RELAY DRIVERS
- MOTOR CONTROL, AUDIO AMPLIFIERS
- DC-DC & DC-AC CONVERTERS

### INTERNAL SCHEMATIC DIAGRAM



SC08140

### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	100	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	100	V
V <sub>GS</sub>	Gate-source Voltage	± 20	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 25 °C	22	A
I <sub>D</sub>	Drain Current (continuous) at T <sub>c</sub> = 100 °C	14	A
I <sub>DM(•)</sub>	Drain Current (pulsed)	88	A
P <sub>tot</sub>	Total Dissipation at T <sub>c</sub> = 25 °C	90	W
	Derating Factor	0.6	W/°C
E <sub>AS(1)</sub>	Single Pulse Avalanche Energy	250	mJ
T <sub>stg</sub>	Storage Temperature	-65 to 175	°C
T <sub>j</sub>	Max. Operating Junction Temperature	175	°C

(•) Pulse width limited by safe operating area

(1) starting T<sub>j</sub> = 25 °C, I<sub>D</sub> = 22A, V<sub>DD</sub> = 50V

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### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1.67	°C/W
R <sub>thj-amb</sub>	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T <sub>I</sub>	Maximum Lead Temperature For Soldering Purpose		300	°C

### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA V <sub>GS</sub> = 0	100			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>c</sub> = 125 °C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			± 100	nA

### ON (\*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	1	1.6	2.5	V
R <sub>D(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 15 A V <sub>GS</sub> = 5 V I <sub>D</sub> = 15 A		0.07 0.085	0.085 0.1	Ω Ω
I <sub>D(on)</sub>	On State Drain Current	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>D(on)max</sub> V <sub>GS</sub> = 10 V	22			A

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>D(on)max</sub> I <sub>D</sub> = 15 A		19		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input Capacitance Output Capacitance Reverse Transfer Capacitance	V <sub>DS</sub> = 25 V f = 1 MHz V <sub>GS</sub> = 0		1750 165 45		pF pF pF

**ELECTRICAL CHARACTERISTICS (continued)****SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 50 \text{ V}$ $I_D = 8 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 4.5 \text{ V}$ (Resistive Load, see fig. 3)		40 80		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 80 \text{ V}$ $I_D = 16 \text{ A}$ $V_{GS} = 10 \text{ V}$		24 55 11	31	nC nC nC

**SWITCHING OFF**

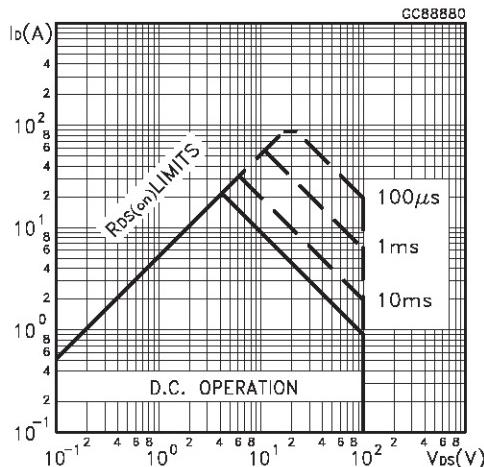
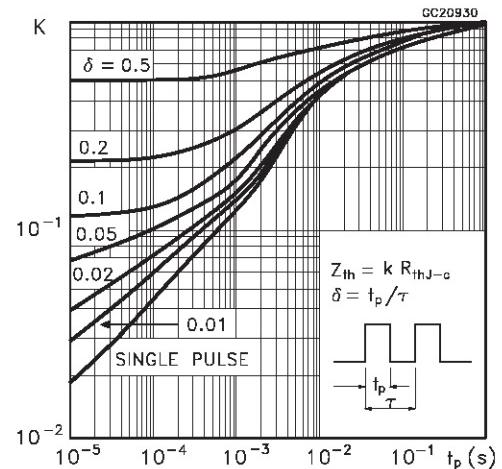
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ $t_f$	Turn-off Delay Time Fall Time	$V_{DD} = 50 \text{ V}$ $I_D = 8 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 4.5 \text{ V}$ (Resistive Load, see fig. 3)		45 12		ns ns
$t_{d(off)}$ $t_f$ $t_c$	Off-voltage Rise Time Fall Time Cross-over Time	$V_{clamp} = 80 \text{ V}$ $I_D = 16 \text{ A}$ $R_G = 4.7 \Omega$ $V_{GS} = 4.5 \text{ V}$ (Inductive Load, see fig. 5)		12 17 35		ns ns ns

**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}(\bullet)$	Source-drain Current Source-drain Current (pulsed)				22 88	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 16 \text{ A}$ $V_{GS} = 0$			1.5	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 16 \text{ A}$ $di/dt = 100 \text{ A}/\mu\text{s}$ $V_{DD} = 40 \text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, fig. 5)		100 300 6		ns nC A

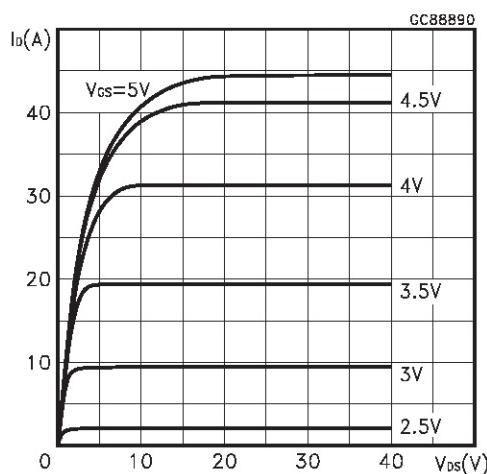
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %

(\*) Pulse width limited by safe operating area

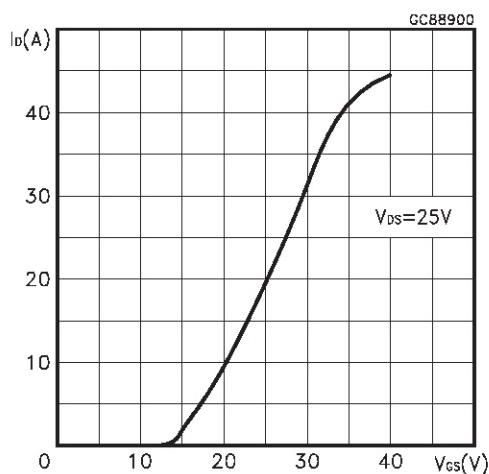
**Safe Operating Area****Thermal Impedance**

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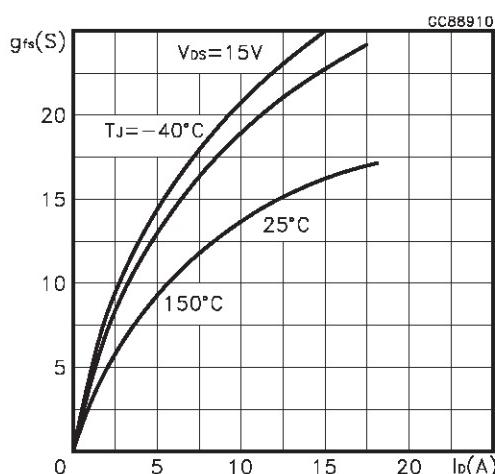
## Output Characteristics



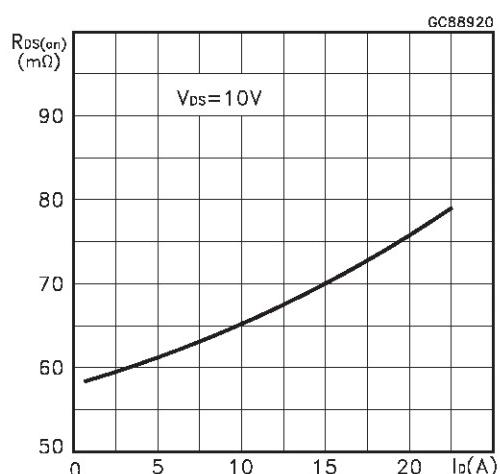
## Transfer Characteristics



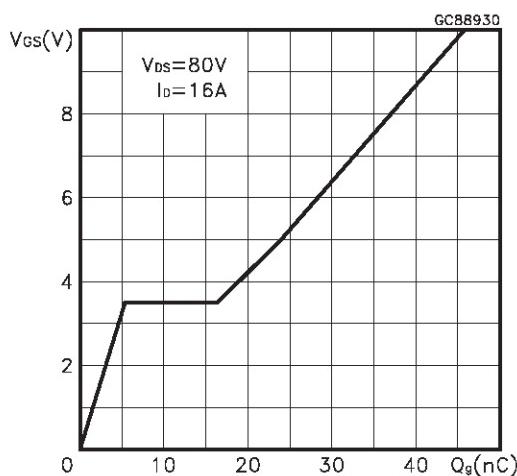
## Transconductance



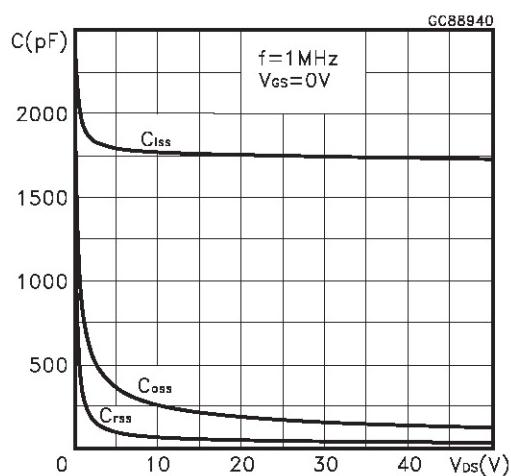
## Static Drain-source On Resistance



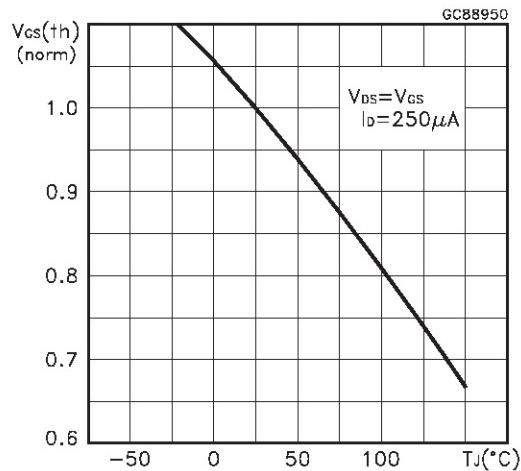
## Gate Charge vs Gate-source Voltage



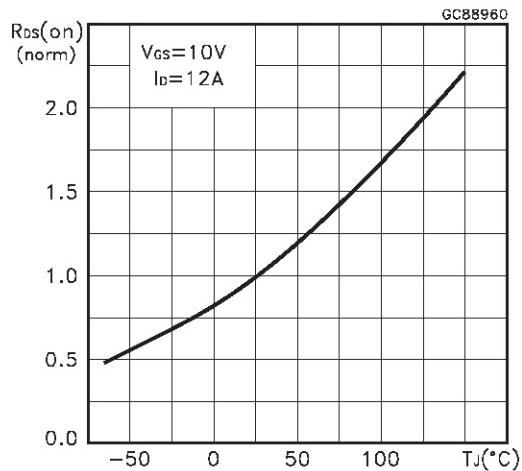
## Capacitance Variations



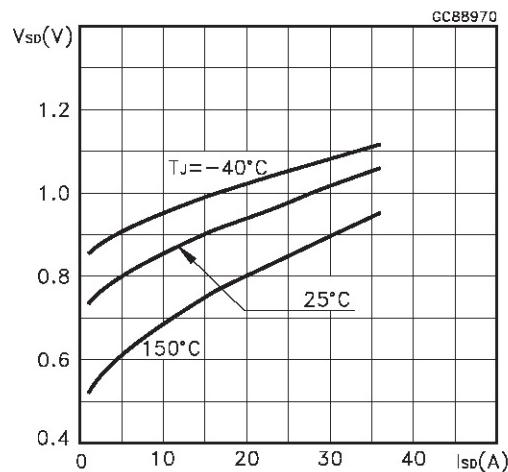
Normalized Gate Threshold Voltage vs Temperature



Normalized On Resistance vs Temperature

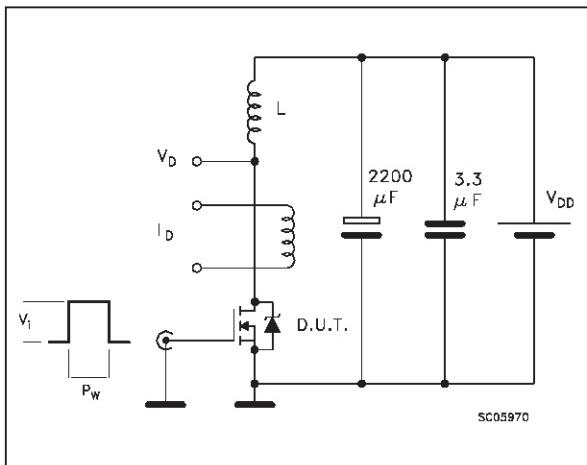


Source-drain Diode Forward Characteristics

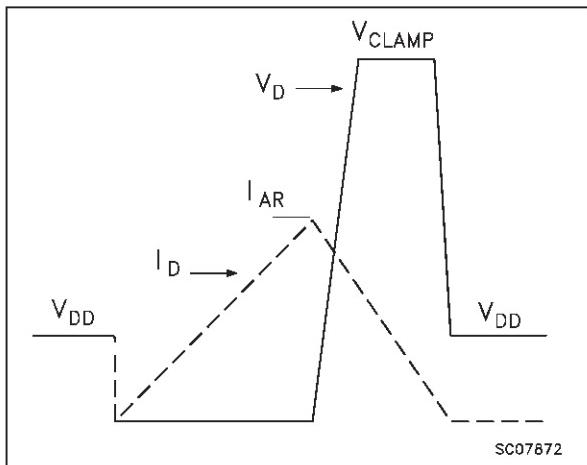


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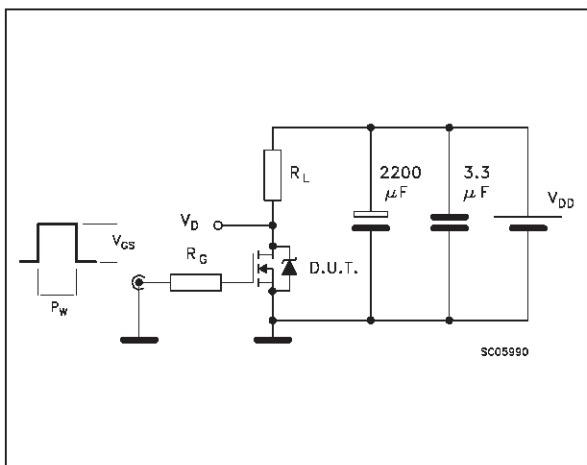
**Fig. 1:** Unclamped Inductive Load Test Circuit



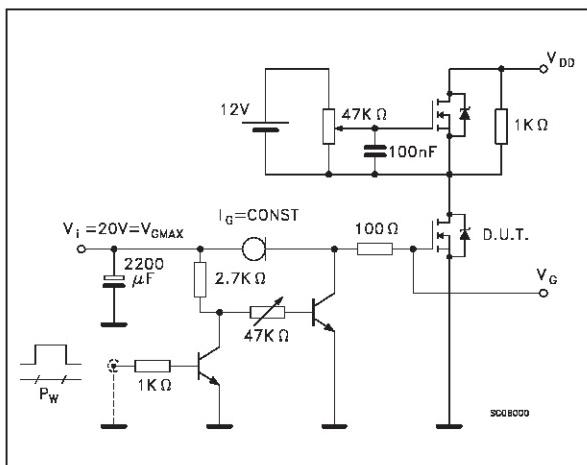
**Fig. 2:** Unclamped Inductive Waveform



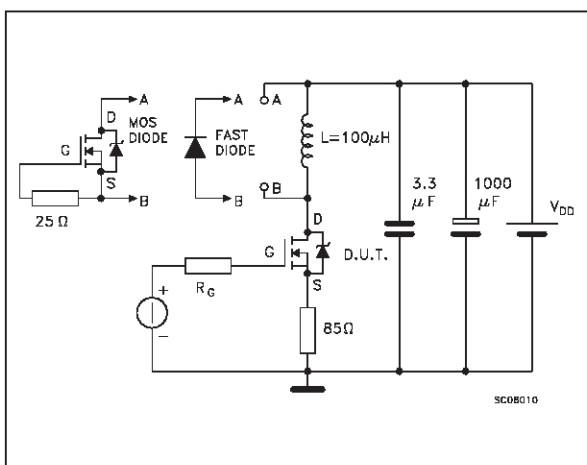
**Fig. 3:** Switching Times Test Circuits For Resistive Load



**Fig. 4:** Gate Charge test Circuit

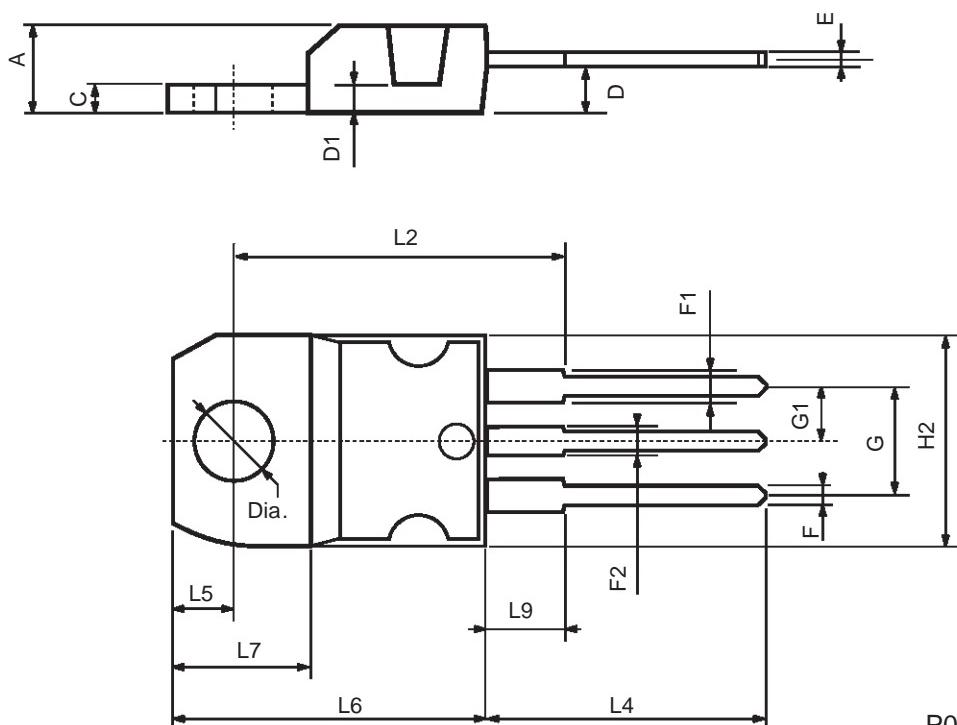


**Fig. 5:** Test Circuit For Inductive Load Switching And Diode Recovery Times



## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



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